

2SB1177

Silicon PNP Epitaxial Planar Type

Power Switching
Complementary Pair with 2SD1747

■ Features

- Low collector-emitter saturation voltage ($V_{CE(sat)}$)
- Good linearity of DC current gain (h_{FE})
- High collector current (I_C)
- "I Type" package configuration with a cooling fin for direct soldering on PC board of a small-size electronic equipment

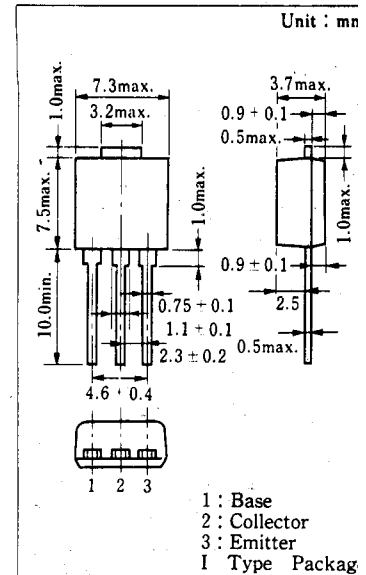
■ Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	-130	V
Collector-emitter voltage	V_{CEO}	-80	V
Emitter-base voltage	V_{EBO}	-7	V
Peak collector current	I_{CP}	-15	A
Collector current	I_C	-7	A
Collector power dissipation	$T_c=25^\circ\text{C}$	15	W
	$T_a=25^\circ\text{C}$	1.3	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -100\text{ V}, I_E = 0$			-10	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-50	μA
Collector-emitter voltage	V_{CEO}	$I_C = -10\text{ mA}, I_B = 0$	-80			V
DC current gain	h_{FE1}	$V_{CE} = -2\text{ V}, I_C = -0.1\text{ A}$	45			
	h_{FE2}^*	$V_{CE} = -2\text{ V}, I_C = -3\text{ A}$	60		260	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5\text{ A}, I_B = -0.25\text{ A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -5\text{ A}, I_B = -0.25\text{ A}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -0.5\text{ A}, f = 10\text{ MHz}$		30		MHz
Turn-on time	t_{on}	$I_C = -3\text{ A},$		0.5		μs
Storage time	t_{stg}	$I_{B1} = -0.3\text{ A}, I_{B2} = 0.3\text{ A},$		1.5		μs
Collector current fall time	t_f	$V_{CC} = -50\text{ V}$		0.1		μs

■ Package Dimensions



*Surface-mount type is also available.
(Refer to p.81.)